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Serial Number 10/695,010
Docket Number YOR920030018US1
Amendment**Amendment to the Specification**

Please replace paragraph [0005] with the following amended paragraph:

[0005] Magnetic memory cells are memory cells that store information in the orientation of the magnetization of a ferromagnetic region. These magnetic memory cells are nonvolatile and can hold stored information for long periods of time. Magnetic memory cells that use a magnetic state to alter the electrical resistance of the materials near the ferromagnetic region are collectively known as magnetoresistive (MR) memory cells. An array of magnetic memory cells is often called magnetic RAM or MRAM (magnetic random access memory). MRAM arrays include an array of magnetic memory cells positioned at the intersections of wordlines and bitlines. Each cell includes a magnetically changeable or free region and a proximate reference region arranged into a magnetic tunnel junction ("MTJ") device. The principle underlying storage of data in such cells is the ability to change the relative orientation of the magnetization of the free and reference regions by changing the direction of magnetization along the easy axis ("EA") of the free region, and the ability to thereafter read this relative orientation difference. More particularly, MRAM cells are written to by reversing the free region magnetization using applied electrical, and resultant magnetic[[,]] stimuli via their ~~its~~ respective bitline and wordline, and are later read by measuring the resultant tunneling resistance ~~between the bitline and wordline~~ their bitlines and wordlines. The tunneling resistance assumes one of two values depending on the relative orientation of the magnetization of the free region with respect to the reference region. If the free region is modeled as a simple elemental magnet having a direction of magnetization which is free to rotate but with a strong preference for aligning in either direction along its easy axis (+EA or -EA), and if the reference region is, for example, a similar elemental magnet but having a direction of magnetization fixed in the +EA direction, then two states (and therefore the two possible tunneling resistance values) are defined for the cell: aligned (+EA/+EA) and anti-aligned (-EA/+EA). These two states may be used to represent a logical "1" or "0" for typical binary processing applications.